Supplementary Information for b000000x

Dynamic Random Access Memory Devices Based on Bismuth Sulfide Nanoplates Prepared from a Single Source Precursor

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Compound	Bi(DTCA) ₃
Formula	$C_{39}H_{24}BiN_3S_6$
Formula weight	935.95
Crystal system	Monoclinic
Space group	P 21/n
a (Å)	16.950(3)
b (Å)	9.6195(15)
c (Å)	20.795(3)
β (°)	93.618(5)
V (Å ³)	3383.7(9)
Ζ	4
Dc(Kg/m ³)	1.837
F(0 0 0)	1832
Crystal size (mm)	0.10 x 0.05 x 0.05
Data/restraints/parameters	7624 / 0 / 443
Goodness-of-fit on F^2	1.141
R1, wR2 (Ι>2σ(Ι))	0.0795, 0.1163

Table S1. Summary of Crystallographic Data for Bi(DTCA)₃

R1, wR2 (all data)

0.1241, 0.1342

Compound Bi(DTCA)₃ Bi(1)-S(1) 2.639(3)Bi(1)-S(3) 2.720(2)Bi(1)-S(4) 2.731(3) Bi(1)-S(2)2.886(3)3.096(3) Bi(1)-S(5)2.963(3)Bi(1)-S(6)88.76(9) S(1)-Bi(1)-S(3)S(1)-Bi(1)-S(4)82.18(9) S(3)-Bi(1)-S(4) 65.19(8) S(1)-Bi(1)-S(2)63.91(9) S(3)-Bi(1)-S(2) S(4)-Bi(1)-S(2) 132.61(9) 81.18(8) 93.08(9) 140.70(8) S(1)-Bi(1)-S(5)S(3)-Bi(1)-S(5)S(4)-Bi(1)-S(5) 76.17(8) 134.05(8) S(2)-Bi(1)-S(5)S(1)-Bi(1)-S(6)86.54(8) S(3)-Bi(1)-S(6)161.40(7) S(4)-Bi(1)-S(6) 131.65(7) S(2)-Bi(1)-S(6) 80.59(8) 57.63(7) S(5)-Bi(1)-S(6)





Fig. S1TG analysis of Bi(DTCA)₃.



Fig. S2 SEM image of Bi_2S_3 samples prepared by solventless method.